

Title (en)

WAFER STRUCTURE FOR ELECTRONIC INTEGRATED CIRCUIT MANUFACTURING

Title (de)

WAFERSTRUKTUR ZUR HERSTELLUNG EINER ELEKTRONISCHEN INTEGRIERTEN SCHALTUNG

Title (fr)

STRUCTURE DE TRANCHE POUR LA FABRICATION DE CIRCUITS INTÉGRÉS ÉLECTRONIQUES

Publication

EP 2748848 A4 20150610 (EN)

Application

EP 12826508 A 20120824

Priority

- US 201113218308 A 20110825
- US 201113218273 A 20110825
- US 201113218335 A 20110825
- US 201113218345 A 20110825
- US 201113218352 A 20110825
- US 201113218292 A 20110825
- US 2012052269 W 20120824

Abstract (en)

[origin: WO2013028973A1] A bonded wafer structure having a handle wafer, a device wafer, and an interface region with an abrupt transition between the conductivity profile of the device wafer and the handle wafer is used for making semiconductor devices. The improved doping profile of the bonded wafer structure is well suited for use in the manufacture of integrated circuits. The bonded wafer structure is especially suited for making radiation-hardened integrated circuits.

IPC 8 full level

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Citation (search report)

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- See references of WO 2013028973A1

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